

Instrumentation Division Report

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Presentation to the DOE RHIC Program Review

July 10, 2003

Outline

- **Core Technologies and Facilities**
- **Key Accomplishments and R&D for future NP Program**



managed by Brookhaven Science Associates for the U.S. Department of Energy

Instrumentation Division

Mission:

“To develop state-of-the-art instrumentation required for experimental research programs at BNL.

To provide limited production quantities of such for BNL-related experiments.”

Core technologies:

- **Semiconductor detectors** (pixel-, drift-, photo sensors);
- **Gas and noble liquid detectors**;
- **Microelectronics** (low noise analog/digital);
- **Lasers and Optics** (ultra-short photon & electron bunches, photocathodes, optical metrology);
- **Micro/nano Fabrication** (sensors, microstructures, e-beam lithography).

Staff:

47 Total

26 Scientists & Professionals

21 Technical & Administrative

Publications in FY 01/02

All Programs: 42

Instrumentation Division

Core Competencies and Program Areas Served

		Nuclear Physics	H. E. Physics	Accelerator Dev.	Chemistry	Material Science	Biology & Medicine	EENS	Industry Collab.
Semiconductor, Gas & Liquid Detectors	X-ray, gamma-ray Detectors (1D, 2D)				✓	✓	✓		
	High Resolution Neutron Detectors			✓		✓	✓		
	Silicon (strip-, pad-, drift-) Detectors	✓	✓	✓	✓	✓	✓	✓	✓
	Cryogenic Detectors	✓	✓						
	Gas Detectors for High Particle Rates and Multiplicities (Cathode Pad/Strip Chambers)	✓	✓	✓	✓	✓			
Micro-electronics	Monolithic and Hybrid Low Noise Amplifiers	✓	✓	✓	✓	✓	✓	✓	✓
	Data Acquisition Electronics	✓	✓		✓	✓	✓	✓	✓
	Fast Noble Liquid Calorimetry Readout	✓	✓						
Lasers, Optics & Microfabrication	Optics Metrology		✓		✓	✓	✓	✓	✓
	Laser and Optics in New Accelerator Concepts: Photocathodes, Fast Pulsed Photocathodes	✓	✓	✓		✓	✓	✓	✓
	Electro-optics and Ultrashort Laser-pulse Techniques (ps — fs → as)	✓	✓	✓		✓			✓
	Micro/nano Fabrication			✓		✓	✓	✓	✓
Total Effort in FY2003 [%]		35	25	40					

Program 04-08

In support of vital BNL programs:

- RHIC Detector Upgrades (silicon and TPC)
- e-cooler; e-RHIC:
 - High Current Photocathodes*
- ATLAS Dets., and LHC upgrade
- Si-detectors for Polarimeters
- Si-detectors & microelectronics:
 - EXAFS at high photon rates*
 - X-ray Microscopy*
 - Protein crystallography*
 - Position sensitive modification*
- New small animal PETs, MRI
- Neutron detectors for SNS
- Neutrino detectors
- Detectors and Microelectronics for
Homeland Security Program

State-of-the-art core technology:

- Fine-grained Si and gas detectors
- Low noise microelectronics from submicron to nanoscale
- Femtosecond, photon and particle beam generation & diagnostics
- Nano-fabrication: pattern generation; deposition/ablation; characterization

Exploration:

- CMOS as direct conversion detectors
- Megapixel matrix on kohm cm Si
- Neutrino (“bubble”) detector
- Femtosecond ~100 eV source

Future Activities for RHIC

S = 1-2 years; M = 3-5 years; L = ≥ 5 years

Time Scale:

Silicon Detectors

- STAR , low mass, e.g., CMOS imagers L
- PHENIX – pixel detectors M-L
- “ -- single sided 2d strip detectors S-M
- Polarimeter II S

Gas Detectors

- Small (“Micro”) TPC M-L

Microelectronics

- Fine-grained detectors S-M-L
- FPGA & DSP technology (STAR DAQ) S-M-L
- Trigger upgrades for PHENIX S-M

RHIC Beam Monitoring

- Digital Signal Processing;
Continuing development

Photocathodes

- Electron cooling at RHIC M
- e – RHIC, GaAs \rightarrow polarized electrons L

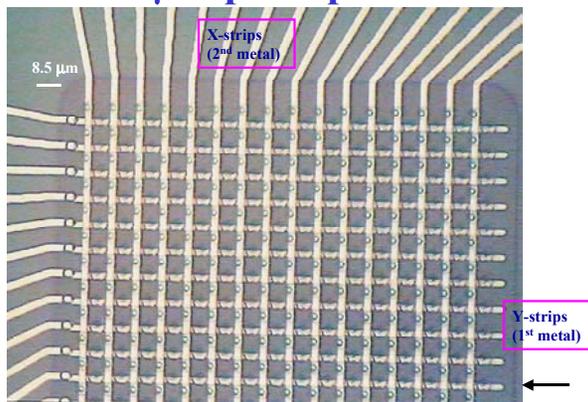
Si Detector Development and Processing at Instrumentation Div.

Novel Detectors

○ Stripixel detectors

2d position sensing
1-sided processing

8.5 μm pitch pixels



○ Active matrix pixel sensors

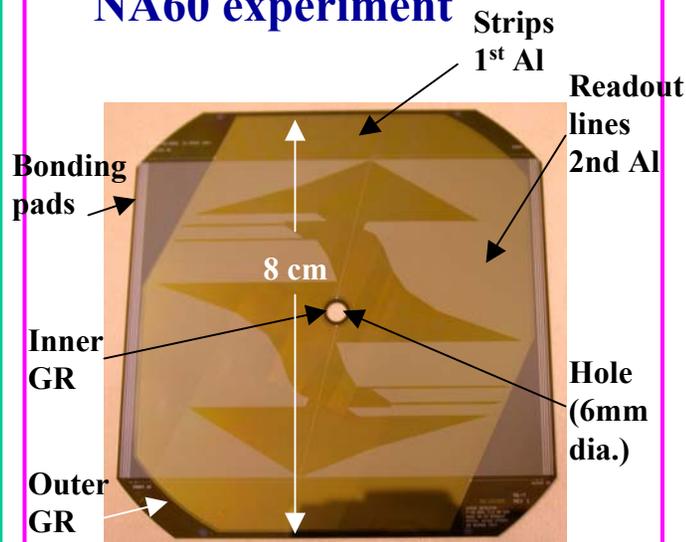
○ Edgeless detectors

○ Semi-3d sensors

for radiation hardness

Prototype Detectors for Existing Experiments

○ Segmented, multi-pitch strip detectors for CERN NA60 experiment



○ Large Roman pot strip detectors for RHIC PP2PP experiment

○ Large stripixel detectors for PHENIX upgrade

Radiation Hard Detectors

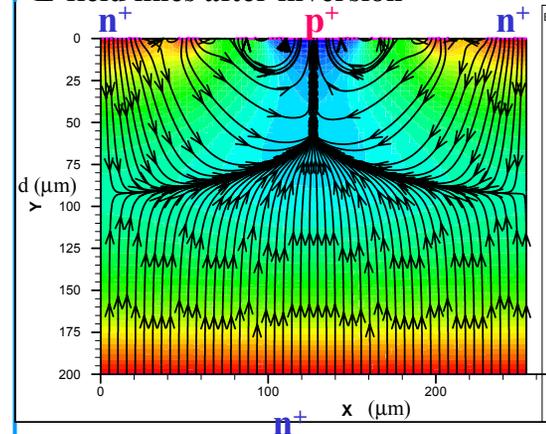
○ Low resistivity detectors

○ Oxygenated detectors

○ Cryogenic Si detectors

○ Detectors with novel structures (semi-3d)

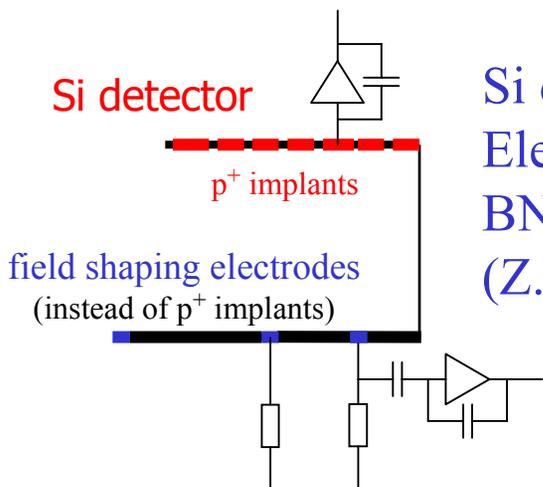
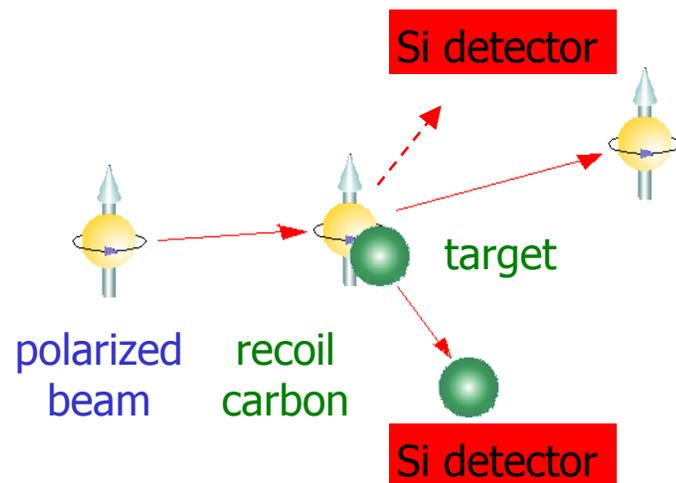
Simulation of potential profile and E-field lines after inversion



○ High resistivity CZ Si detectors

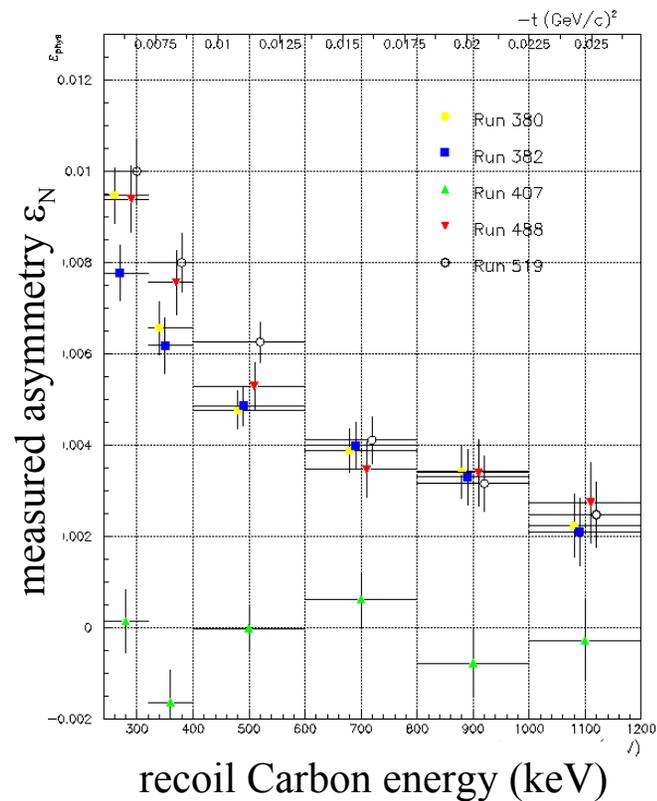
SPIN POLARIMETER for RHIC and AGS

Measure the beam polarization at RHIC and AGS by measuring the left-right spin asymmetry of polarized protons scattering off a carbon (proton) target by detecting the the low energy recoil carbons (protons) with Si detectors.



Si detectors and Front End Electronics Developed at BNL Instrumentation Division (Z. Li & S. Rescia)

1. RHIC polarimeter installed in 2002
2. AGS polarimeter installed in 2003
3. RHIC absolute polarimeter using a double-sided strip detector under development for 2004

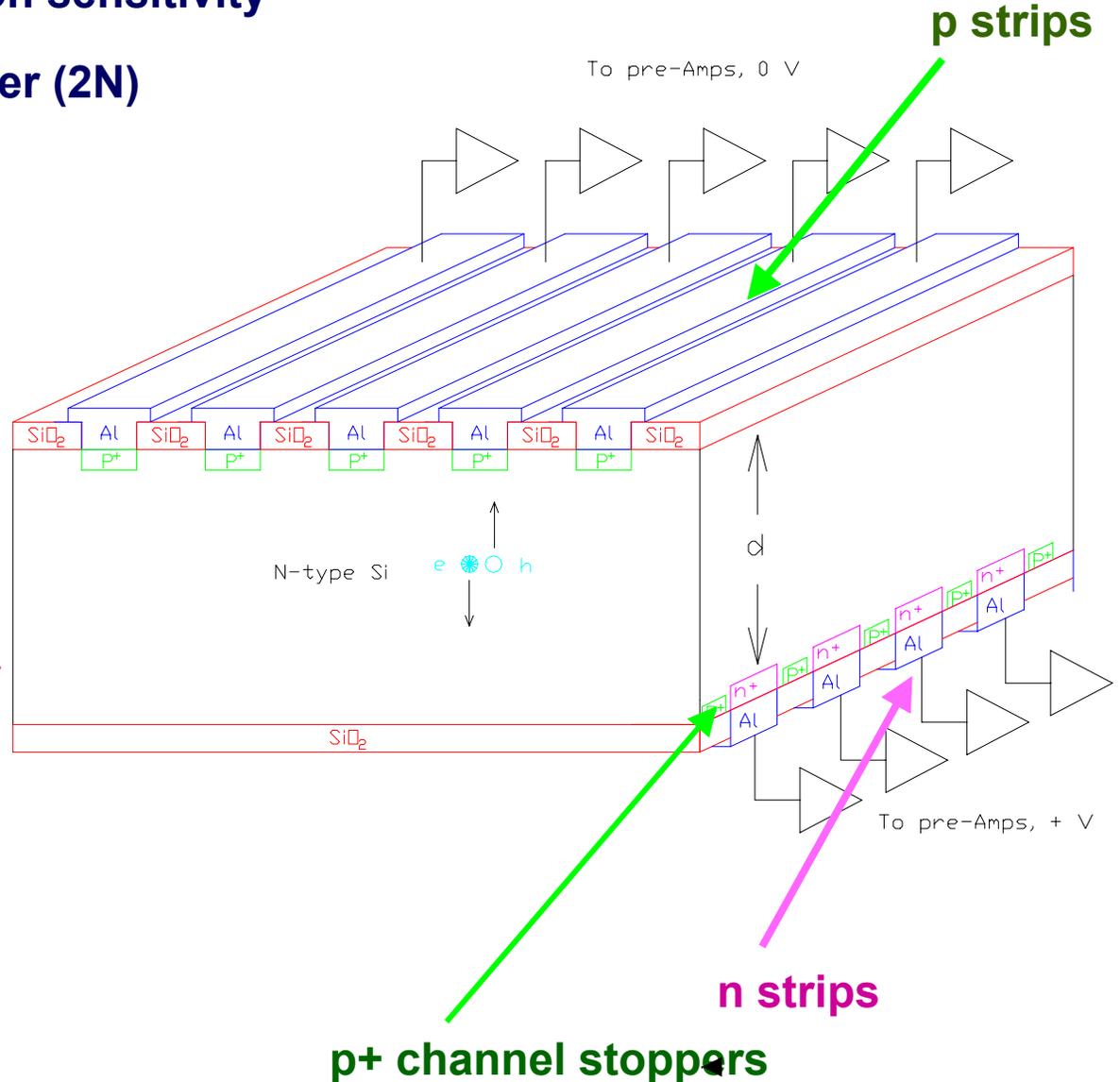


Double-sided strip detectors on high resistivity silicon ($\sim 3\text{-}5\text{ kohm cm}$):

- Two dimensional position sensitivity
- Minimum channel number ($2N$)

But:

- *Two-sided process about 3-4 times more complicated/expensive than single-sided process*
- *Radiation soft due to the the complicated structure on the n-side*
- *Two polarities of readout electronics*

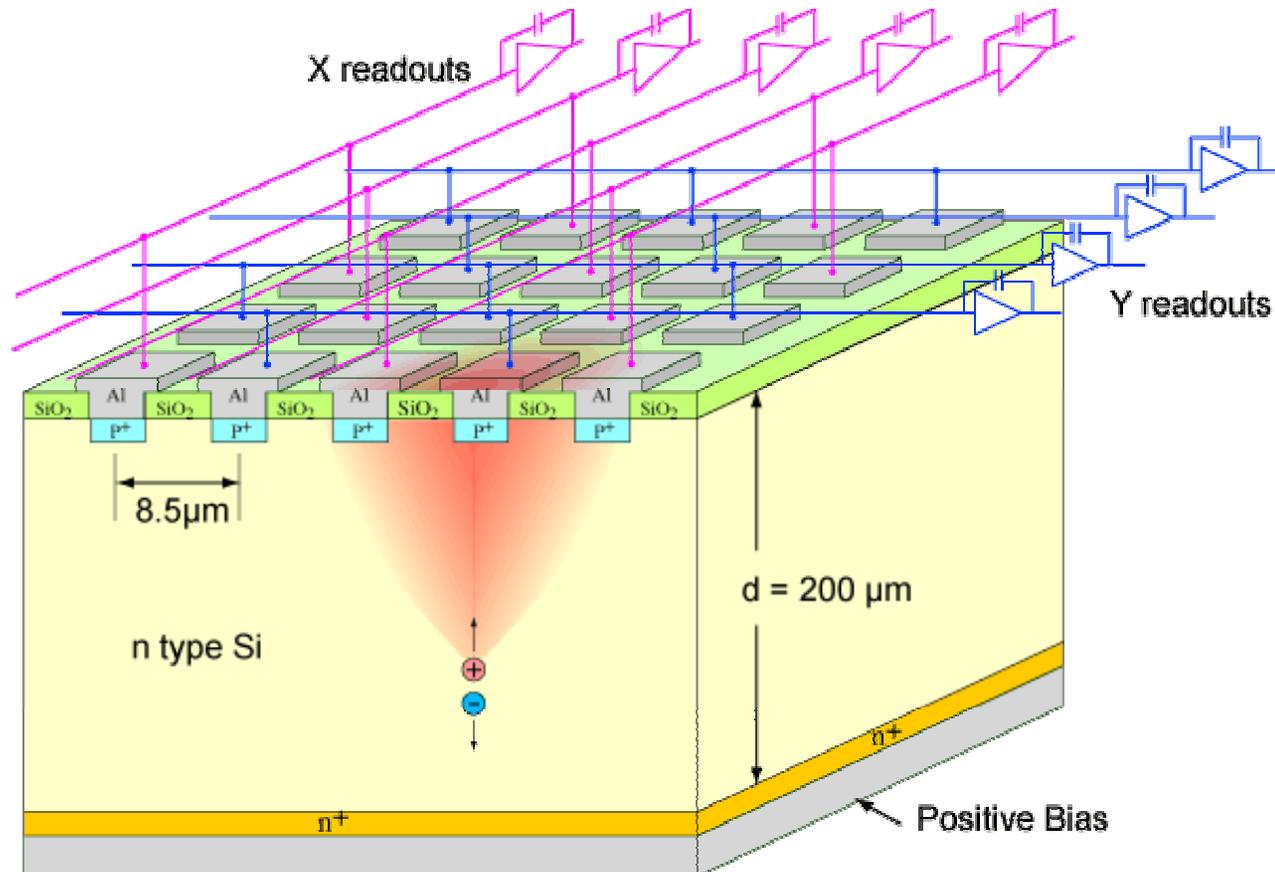


The new concept:

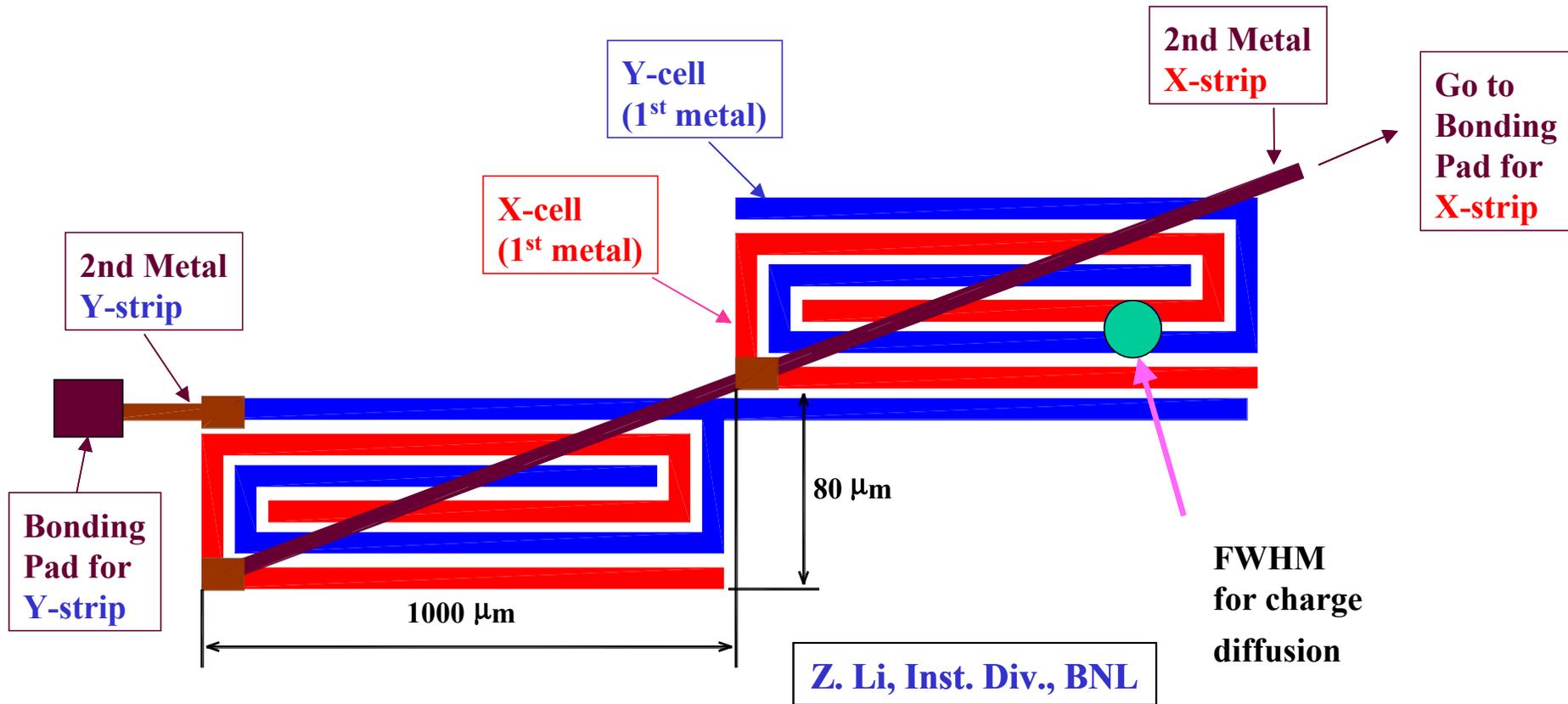
Alternating **stripixel** detectors (ASD)

Individual **pixels** are alternately connected by X and Y readout lines (**strips**)

- Two dimensional position sensitivity is achieved by charge sharing between X and Y pixels
- In principle, the pixel pitch should not be larger than the size of charge cloud caused by diffusion process



Schematic of the Prototype Stripixel Detector For PHENIX Upgrade

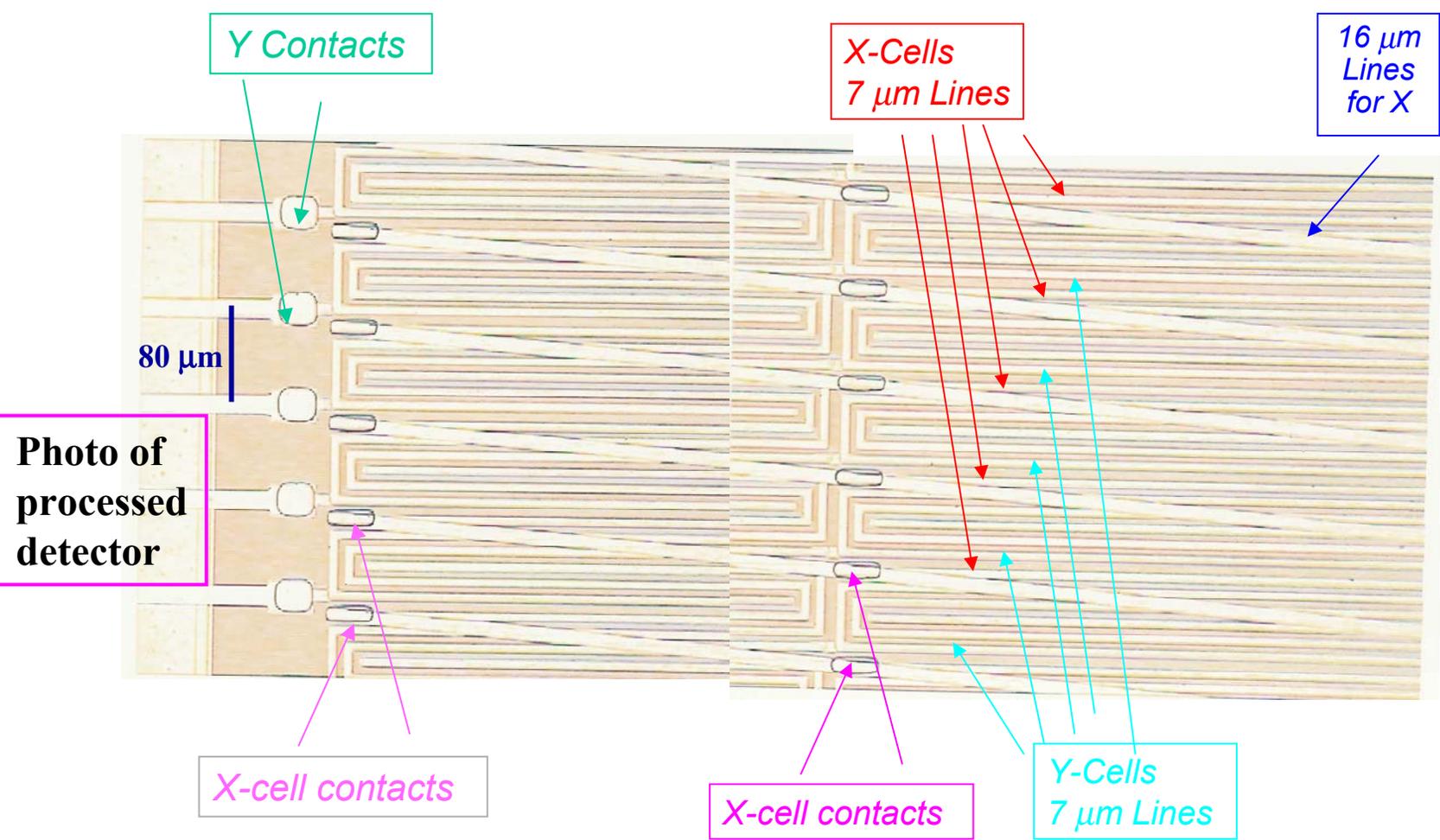
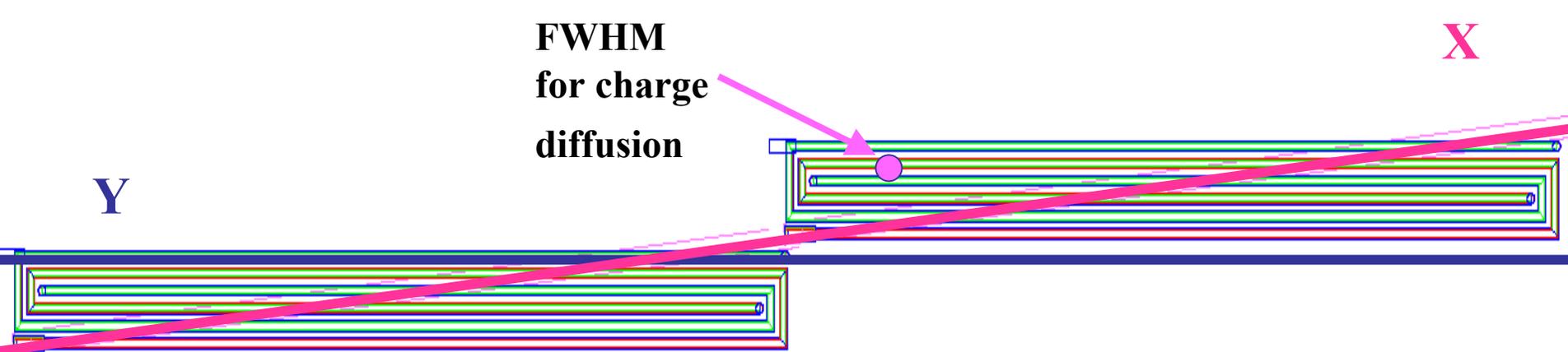


Pixel pitches: 1000 μm in **X**, and 80 μm in **Y**

Pixel arrays: 30x384

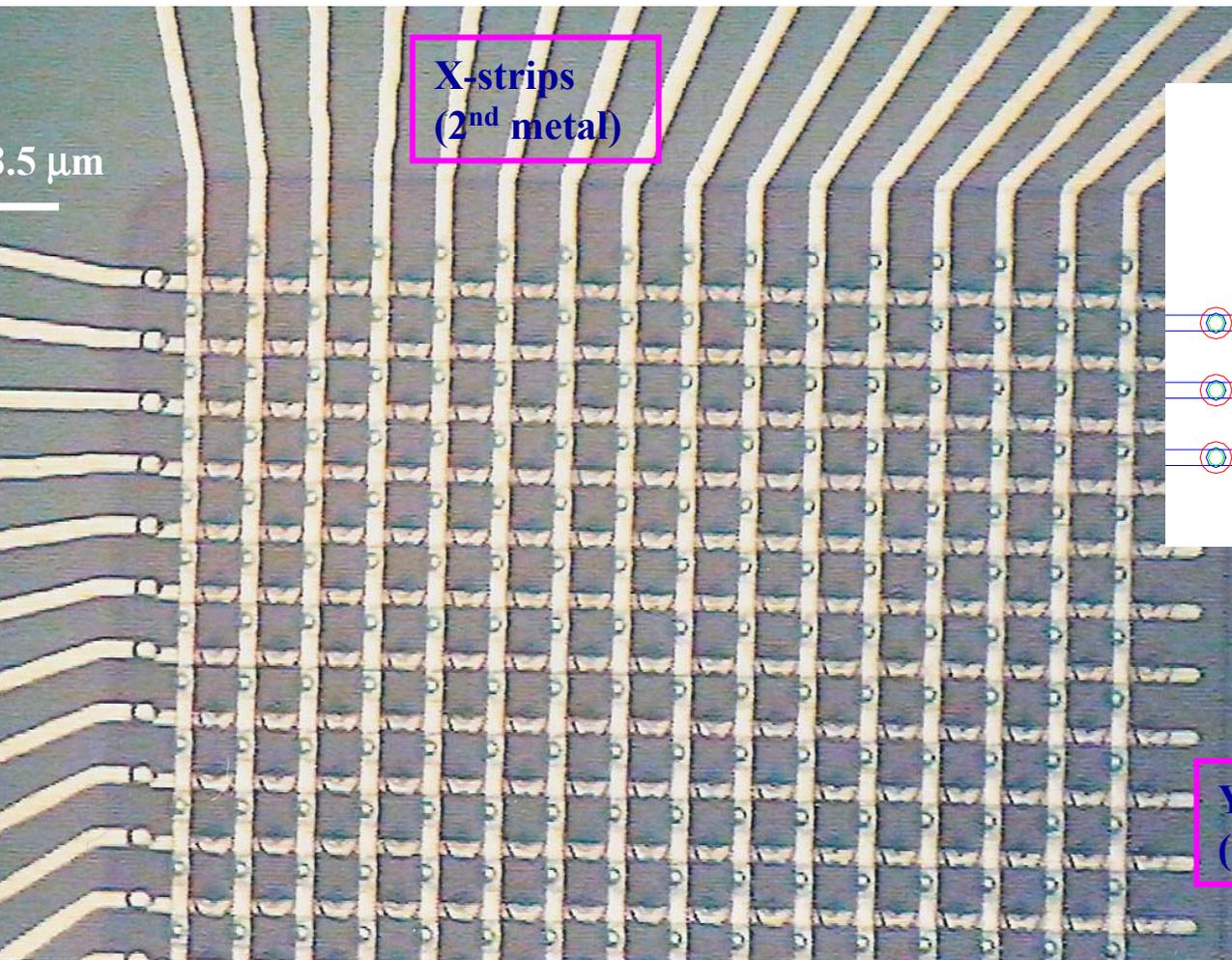
4.6° stereo angle between **X** and **Y** strips

$\sigma_y = \sim 25 \mu\text{m}$

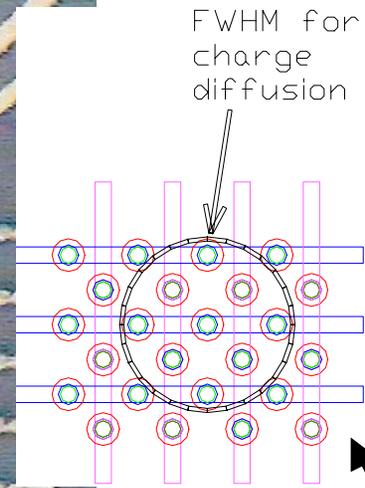


Novel Stripixel Detector for *Sub-micron* Position Resolution in Two Dimensions with One-sided Process

8.50 μm pitch in both X and Y strips



X-strips
(2nd metal)

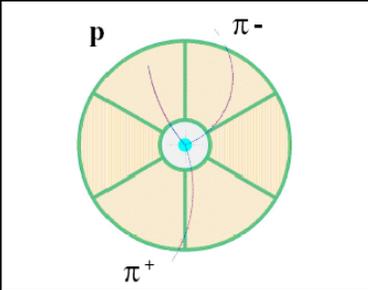
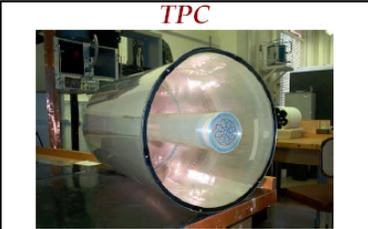
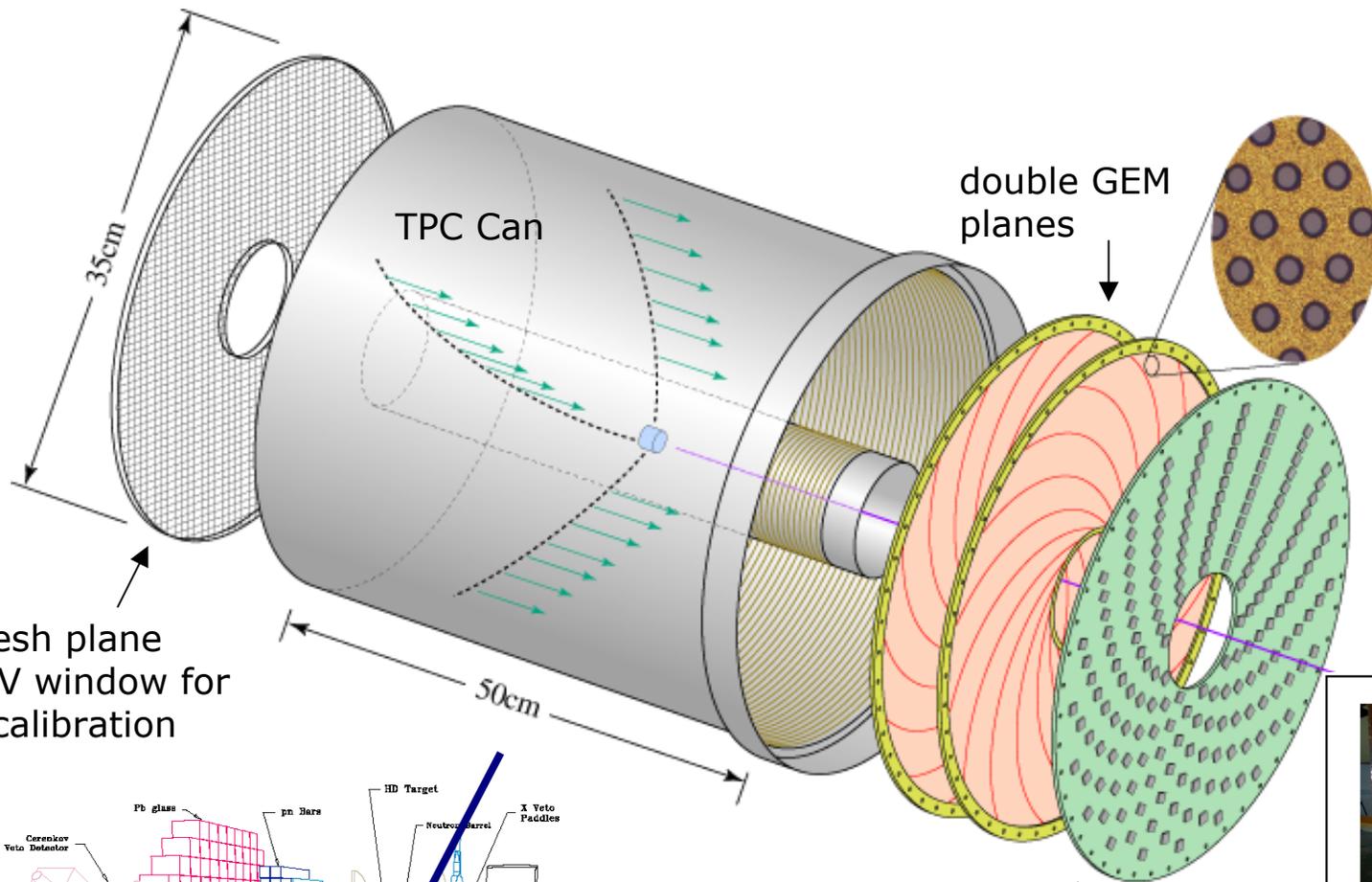


Design and illustration
of diffused charge cloud

Y-strips
(1st metal)

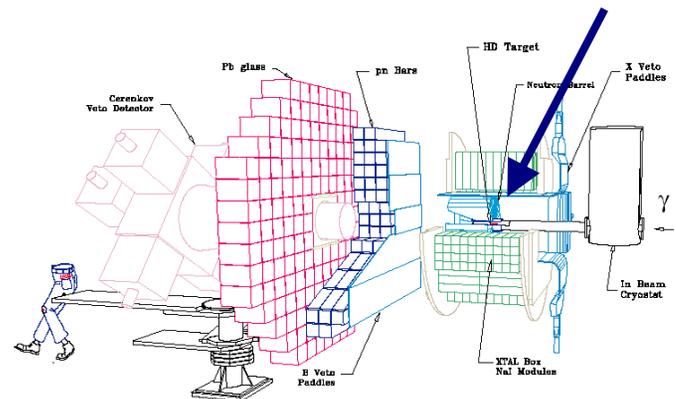
Photo of processed
detector

Laser Electron Gamma Source : Time Projection Chamber (TPC)



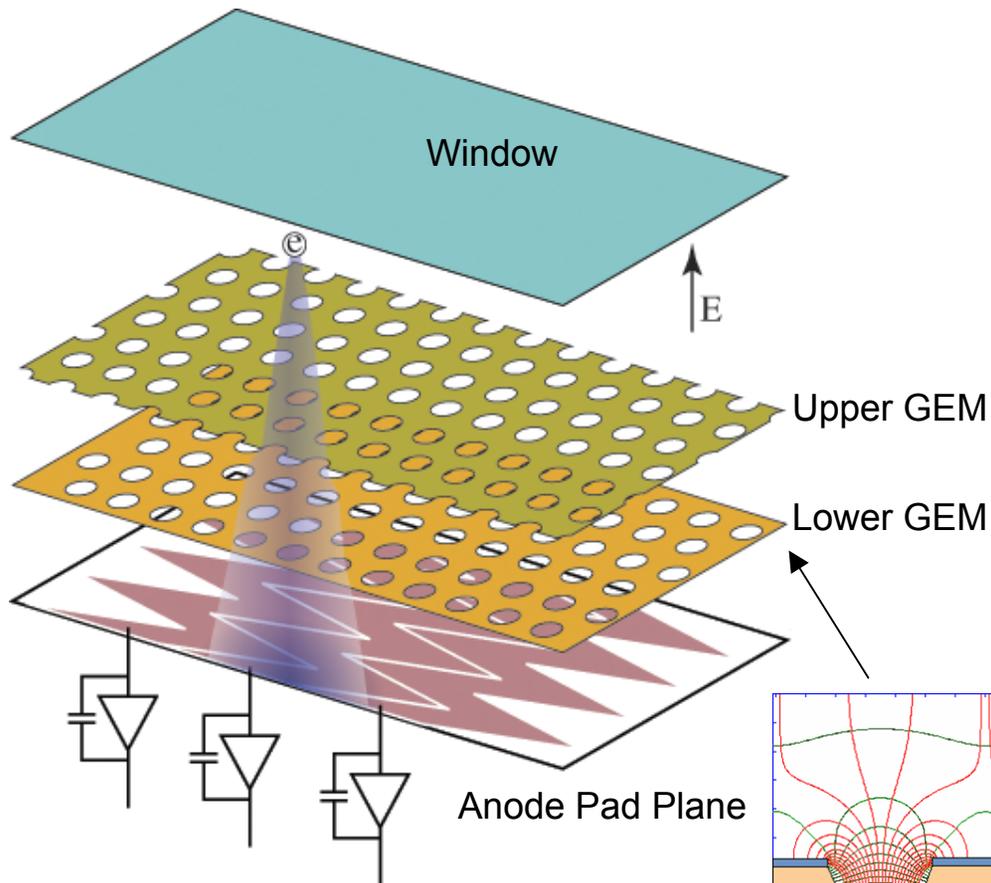
anode pad plane with **front-end electronics**

HV mesh plane and UV window for laser calibration

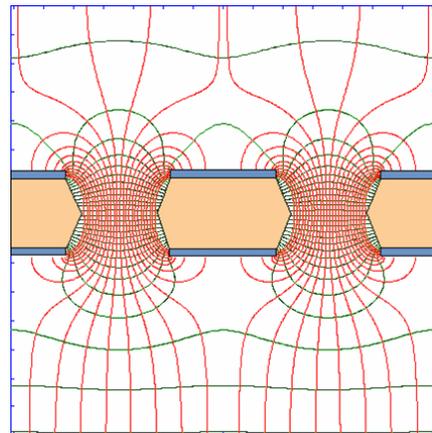
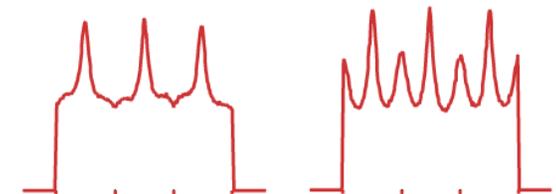
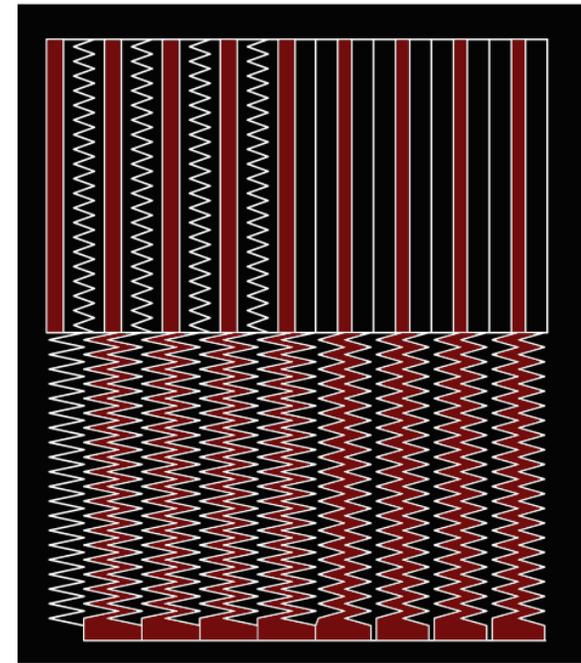


Spin **ASY**mmetry Array (SASY)

Interpolating Pad Readout for GEM (Gas Electron Multiplier)

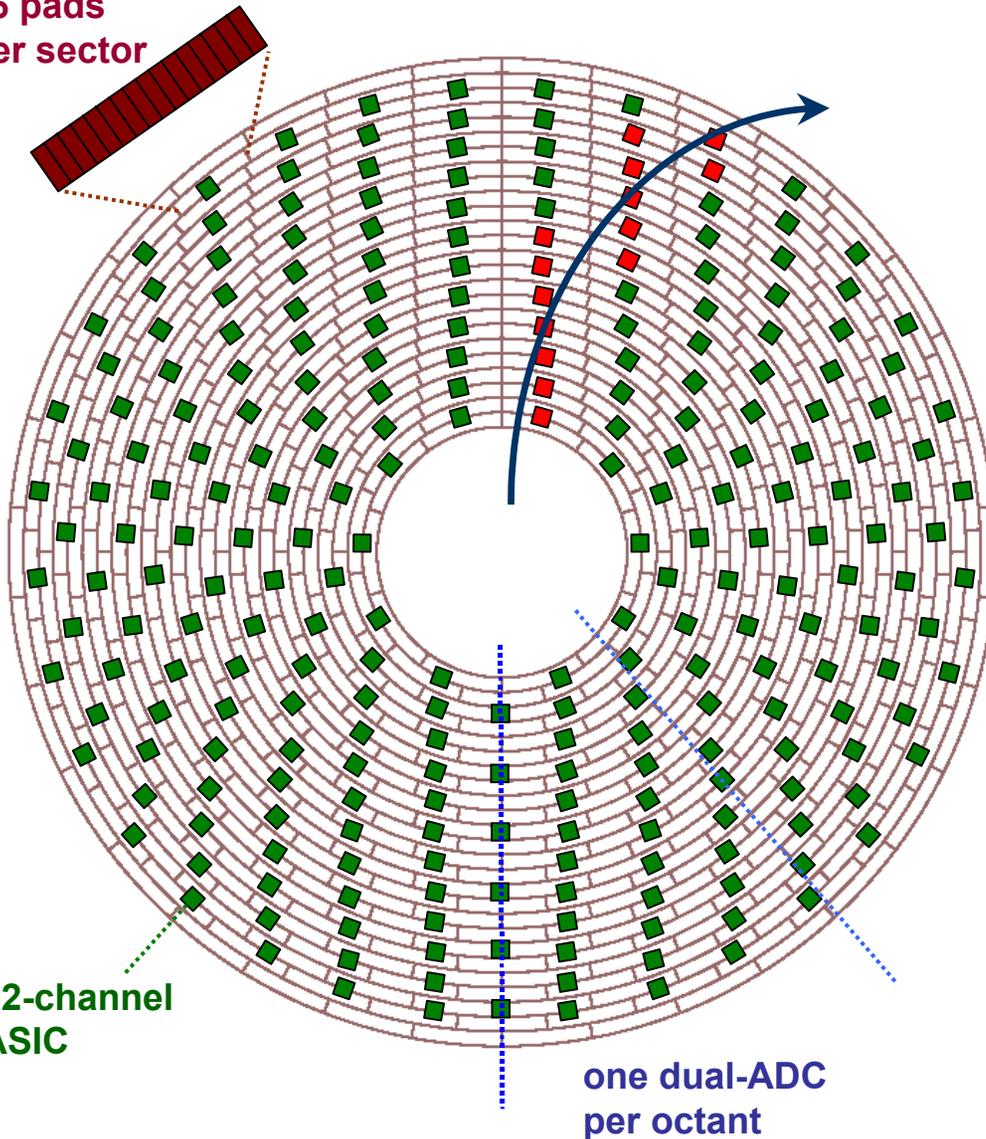


<100 μ m rms
position
resolution
with 2mm pad
pitch



Readout Electronics – Specifications

16 pads
per sector



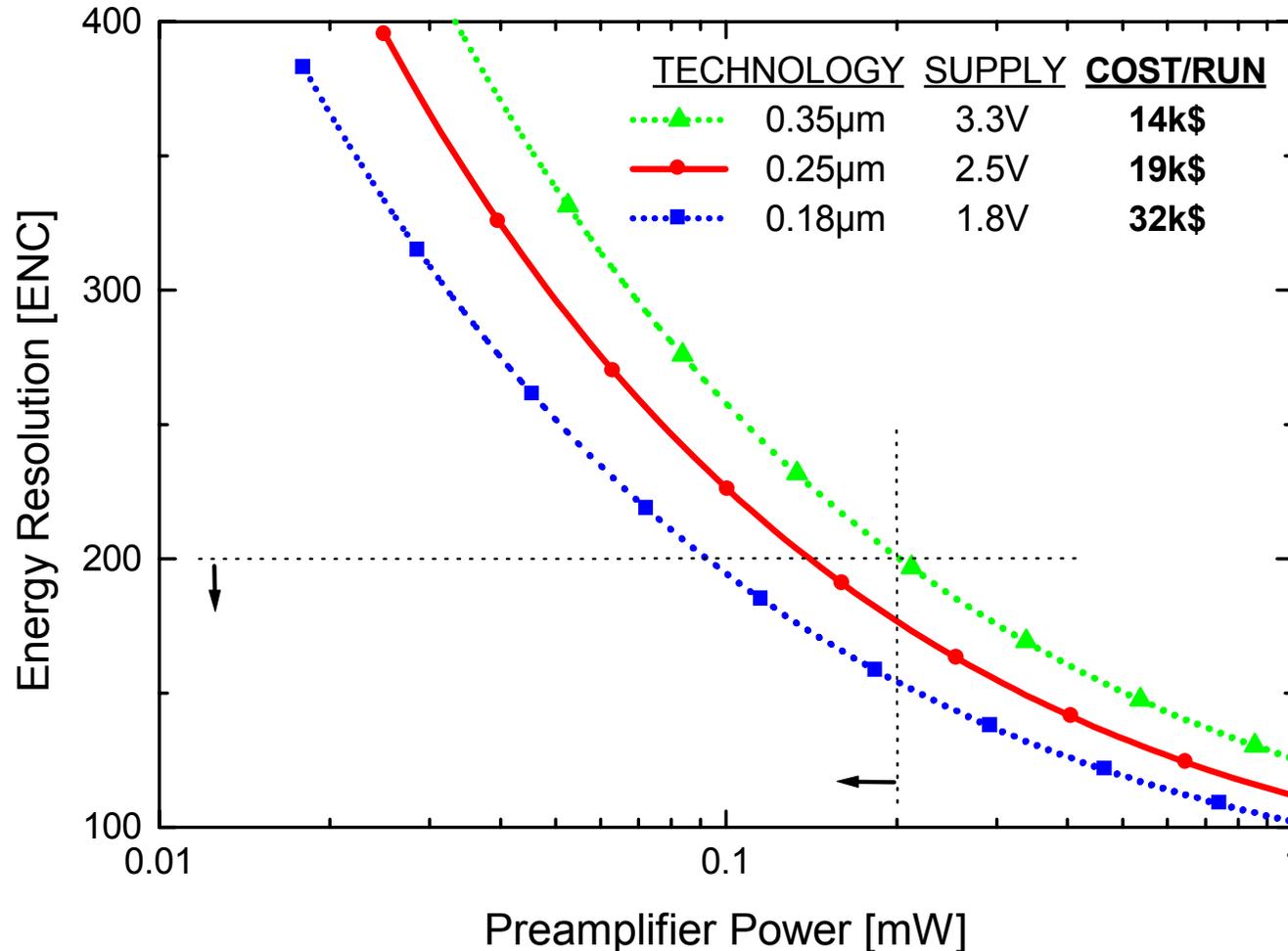
Tracking Measurement

- Energy - triggered pad (xy)
- Energy - neighbor pads (xy)
- Timing (z)

Specifications

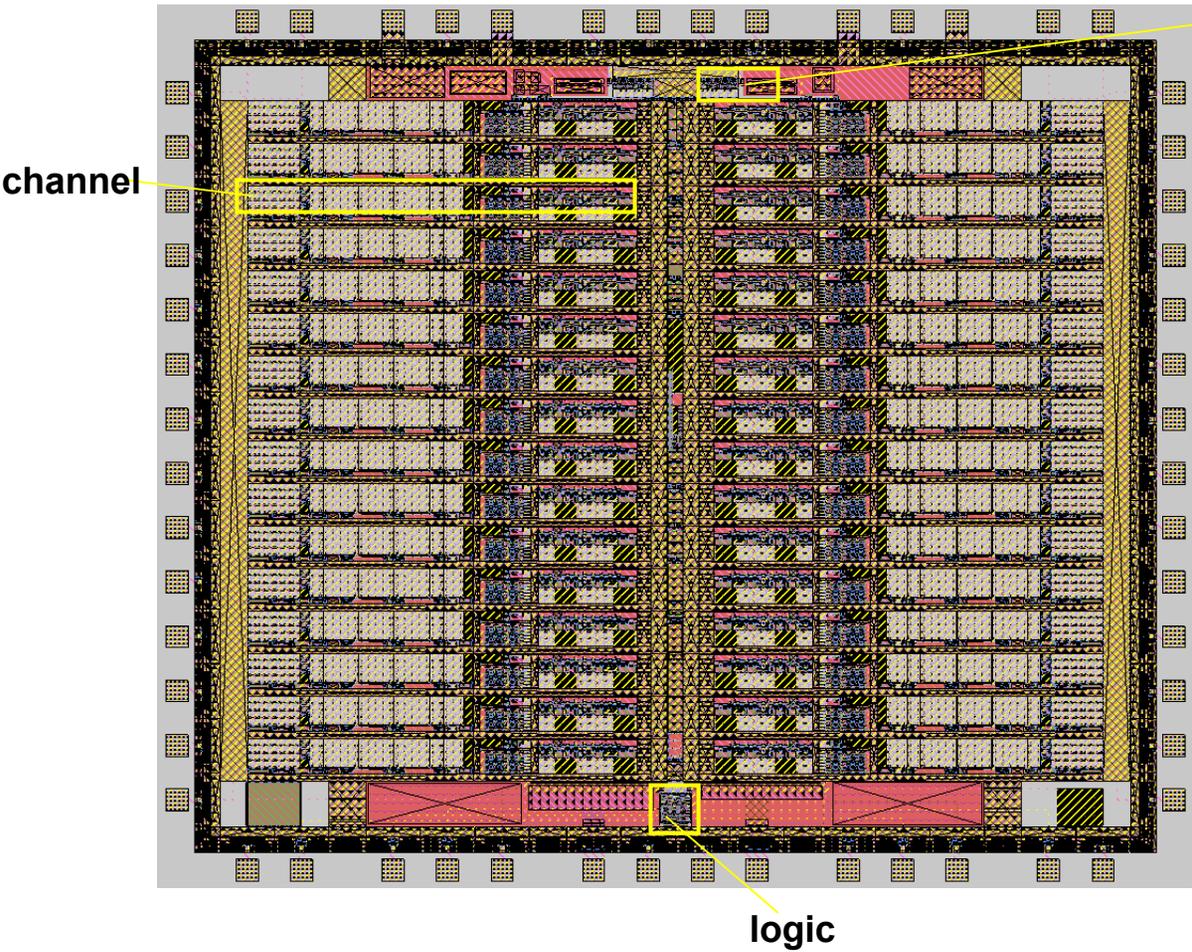
- ENC < 500 e⁻ rms
- Timing < 20ns
- Preamplifier/shaper/BLH
- Peak-detector
- Timing-detector (TAC)
- On-chip buffers
- Neighbor channel/chip enable
- Adjustable gain ≈ 17-32 mV/fC
- Channel masking
- Calibration
- Token/flag readout

Front-End Electronics – Preamplifier Power

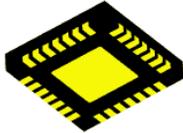


- 32-channel ASIC - layout is pad-limited $\approx 3 \times 3 \text{ mm}^2$
- power / channel $\approx 1 \text{ mW}$ (preamplifier $< 200 \mu\text{W}$)
- energy resolution < 250 rms electrons (600ns peaking time, 5pF)

Layout

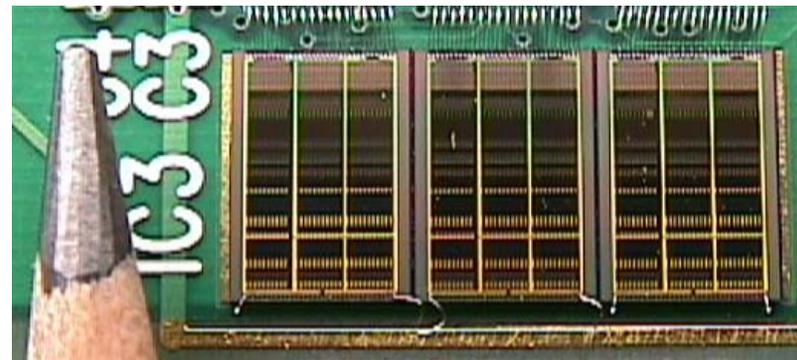
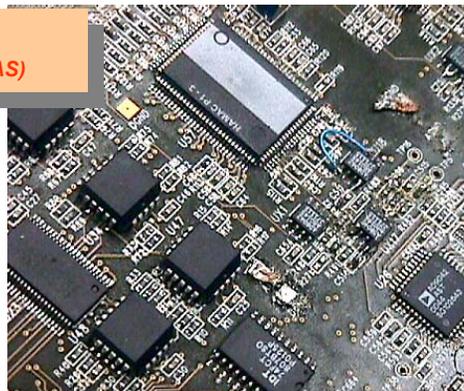
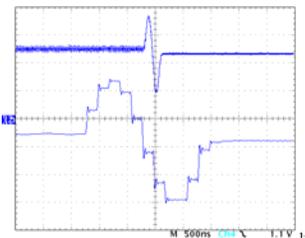


buffer



- 32 channels
- 3.1 x 3.6 mm²
- 47k MOSFETs
- 43mW

High-speed, radiation-tolerant sampling/digitizing board (ATLAS)



Photon-counting ASIC for EXAFS (NSLS)

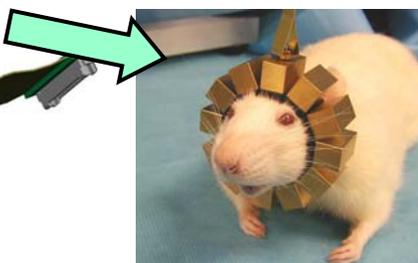
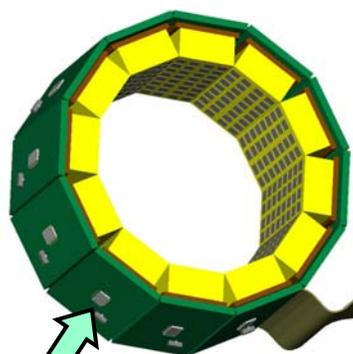


240-channel multichip module for Si drift detector readout (STAR)

Microelectronics Group

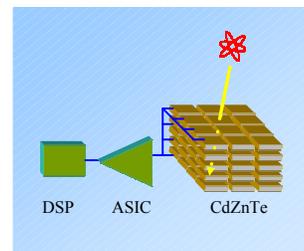
AREAS OF EXPERTISE

- CMOS monolithic circuits
- charge-sensitive sensor interface
- analog signal processing
- low noise, low power techniques
- VLSI custom design + layout

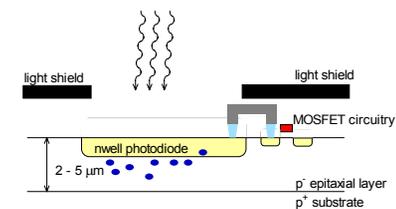


Positron emission tomograph for imaging the awake animal brain

Handheld imaging probe for intra-operative cancer detection (eV Products)

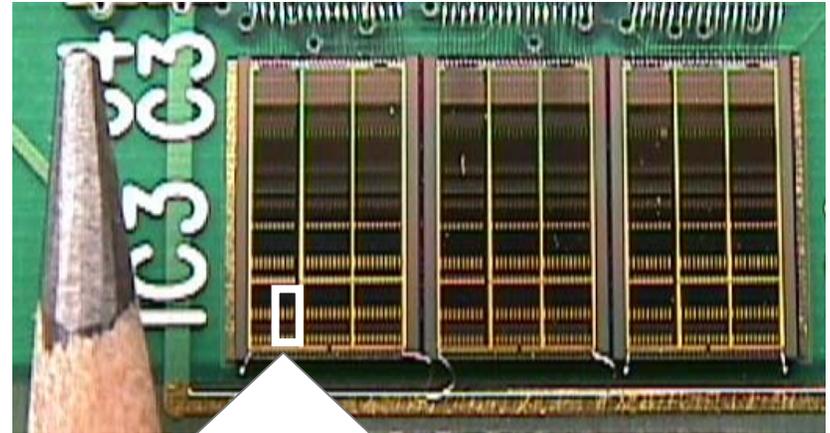


Proposed gamma spectrometer for detection of nuclear materials

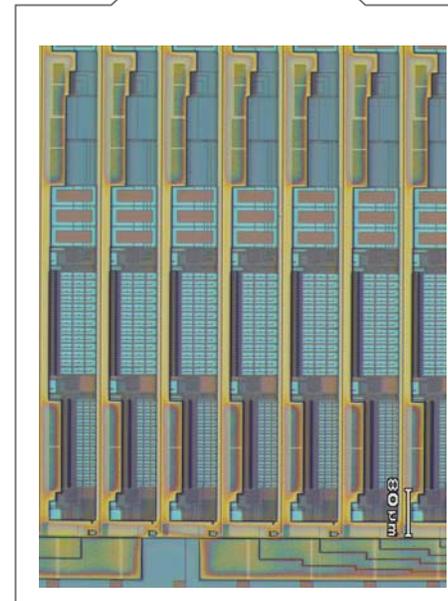
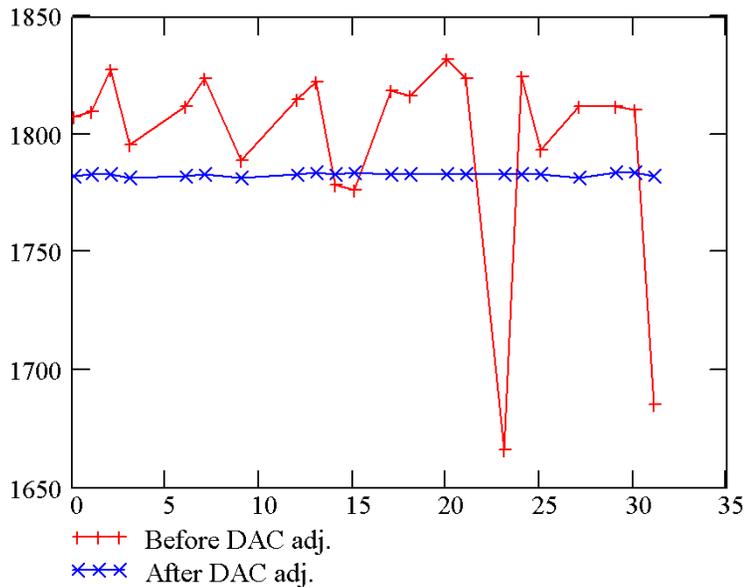


Photon-counting ASIC for EXAFs

- 32-channel 0.35 mm CMOS ASIC
- Wirebonded to 96-channel cooled Si pad detector, 1 x 1 mm pads, 0.8 pF
- 235 eV FWHM (28 e- rms) at 100 kcounts/pad/s
- **180,000 MOSFETs**
- 8.2 mW/chan



Thresholds before and after DAC adjustment

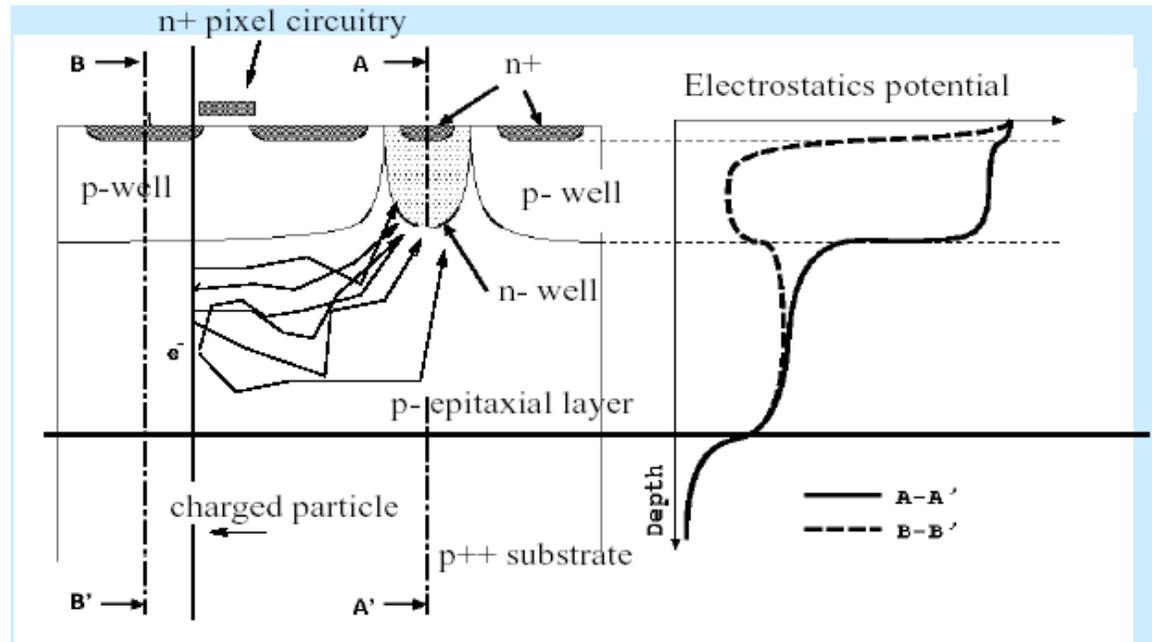


CMOS as Direct Conversion Megapixel Detectors (10-20 μm pixels)

Epitaxial layer $\sim 5\text{-}15\ \mu\text{m}$

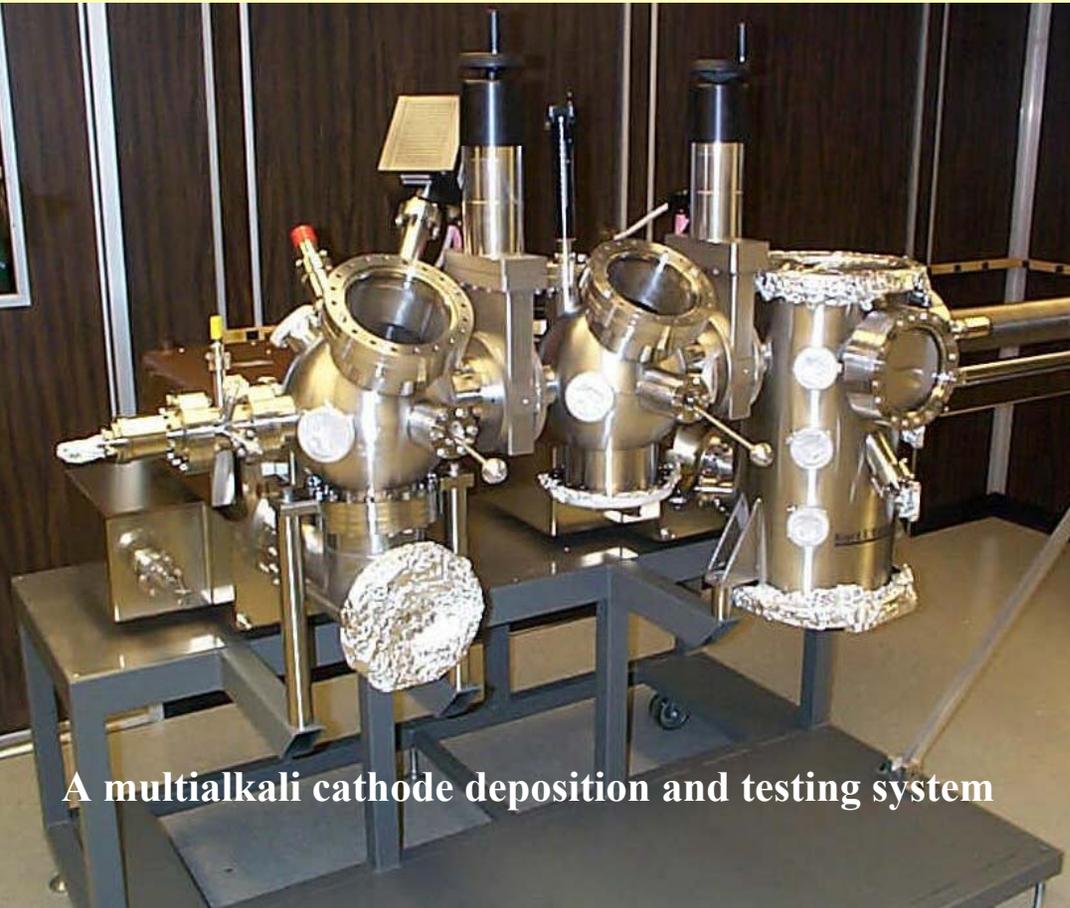
Min. ion. particles $\sim 80\ \text{e}/\mu\text{m}$

Twin - tub (double well),
CMOS process with
epitaxial layer



- The effective charge collection is achieved through the thermal diffusion mechanism,
- The device can be fabricated using a standard, cost-effective and easily available CMOS process,
- The charge generated by the impinging particle is collected by the n-well/p-epi diode, created by the floating n-well implantation,

Multialkali Photocathode Development for *e-cooling*



A multialkali cathode deposition and testing system

GOALS:

- ELECTRON BEAM PARAMETERS:
CHARGE 10 nC, PRF 10 MHz,
AVERAGE CURRENT 100 mA
- QUANTUM EFFICIENCY: FEW %
FOR VISIBLE PHOTONS
- LIFETIME: >8 HRS AT A VACUUM
OF 1×10^{-9} TORR

INVESTIGATE:

- LIFE TIME AS A FUNCTION OF
PRESSURE AND CONTAMINANT
- POSSIBILITY OF IN SITU
REJUVENATION

R&D Program Summary, FY2004-8:

This program utilizes the BNL Instrumentation Division's unique expertise to develop key elements of next generation detectors in support of NP research. It incorporates R&D efforts in *semiconductor detectors, microelectronics, gas detectors and photocathodes*:

- To conduct R&D of novel semiconductor detectors for NP experiments;
To provide insight into the radiation damage problem in Si detectors and to develop radiation hard materials/detectors;
- To conduct an in-depth study of submicron CMOS devices, circuits, DSPs and FPGAs focusing on the front-end electronics, and data acquisition needs of next-generation nuclear physics detectors;
- To develop high density, low mass chip-to-detector (and chip-to-chip) interconnects, and to strengthen the design capabilities in advanced hybrid and printed circuits;
- To develop techniques for fine-grained Time Projection Chambers for NP experiments.
- To develop photocathode technology for e-cooling at RHIC.

While the work in support of the RHIC program represents ~35-40% of our effort, it will benefit greatly from the technologically related work for other BNL programs (LHC, NSLS, PET, etc.).